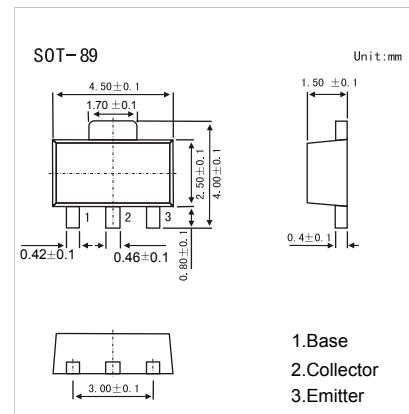


PNP Transistors

PXT2907A (KXT2907A)

■ Features

- Switching and Linear Amplification
- High Current and Low Voltage
- Complement to PXT2222A



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	-60	V
Collector - Emitter Voltage	V _{CEO}	-60	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _c	-600	mA
Collector Power Dissipation	P _c	500	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	250	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _c = -1 mA, I _e = 0	-60			V
Collector-emitter breakdown voltage	V _{CEO}	I _c = -10 mA, I _b = 0	-60			
Emitter-base breakdown voltage	V _{EBO}	I _e = -1 mA, I _c = 0	-5			
Collector-base cut-off current	I _{cbo}	V _{CB} = -50 V, I _e = 0			-50	nA
Emitter cut-off current	I _{ebo}	V _{EB} = -5V, I _c = 0			-50	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-500 mA, I _b =-50mA			-1.6	V
		I _c =-500 mA, I _b =-15mA			-0.4	
Base-emitter saturation voltage	V _{BE(sat)}	I _c =-500 mA, I _b =-50mA			-2.6	
		I _c =-500 mA, I _b =-15mA			-1.3	
DC current gain	h _{FE(1)}	V _{CE} = -10V, I _c = -0.1mA	75			
	h _{FE(2)}	V _{CE} = -10V, I _c = -1mA	100			
	h _{FE(3)}	V _{CE} = -10V, I _c = -10mA	100			
	h _{FE(4)}	V _{CE} = -10V, I _c = -150mA	100		300	
	h _{FE(5)}	V _{CE} = -10V, I _c = -500mA	50			
Delay time	t _d				12	ns
Rise time	t _r	V _{CC} =-30V, I _c =-150mA I _{b1} =- I _{b2} = -15mA			30	
Storage time	t _s				300	
Fall time	t _f				65	
Transition frequency	f _t	V _{CE} = -10V, I _c = -20mA, f=100MHz	200			MHz

■ Marking

Marking	*2F
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